N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

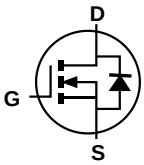
- Low On-Resistance:
  $R_{DS(ON)}$ < 88mΩ @ V_{GS} = 4.5V
  $R_{DS(ON)}$ < 138mΩ @ V_{GS} = 2.5V
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

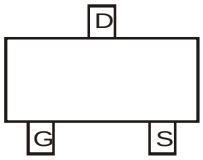
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

SOT323

Top View



Internal Schematic



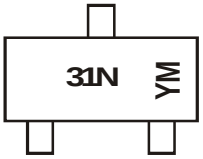
Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3150LW-7	SOT323	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



31N = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: D = 2016)
M = Month (ex: 9 = September)

Date Code Key

Year	2008	~	2016	2017	2018	2019	2020	2021	2022	2023
Code	V	~	D	E	F	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V_{DSS}	28	V
Gate-Source Voltage		V_{GSS}	±12	V
Drain Current (Note 5)	T_A = +25°C T_A = +70°C	I_D	1.6 1.2	A
Drain Current (Note 5)	Pulsed	I_{DM}	6.4	A
Body-Diode Continuous Current (Note 5)		I_S	1.5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	350	mW
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 5)	$R_{\theta JA}$	357	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	28	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	800	nA	V_{DS} = 28V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±80 ±800	nA	V_{GS} = ±12V, V_{DS} = 0V V_{GS} = ±19V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.62	0.94	1.4	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	— —	73 115	88 138	mΩ	V_{GS} = 4.5V, I_D = 1.6A V_{GS} = 2.5V, I_D = 1.2A
Forward Transconductance	$\|Y_{fs}\|$	—	5.4	—	S	V_{DS} = 5V, I_D = 2.7A
Source-Drain Diode Forward Voltage	V_{SD}	—	—	1.16	V	V_{GS} = 0V, I_S = 1.5A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	305	—	pF	V_{DS} = 5V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	74	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	48	—	pF	

Notes: 5. Device mounted on 1in^2 FR-4 PCB on 2oz. Copper. t ≤ 10 sec.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

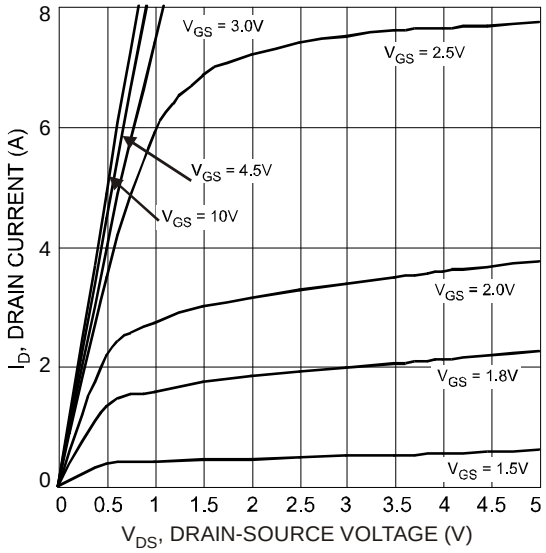


Fig. 1 Typical Output Characteristics

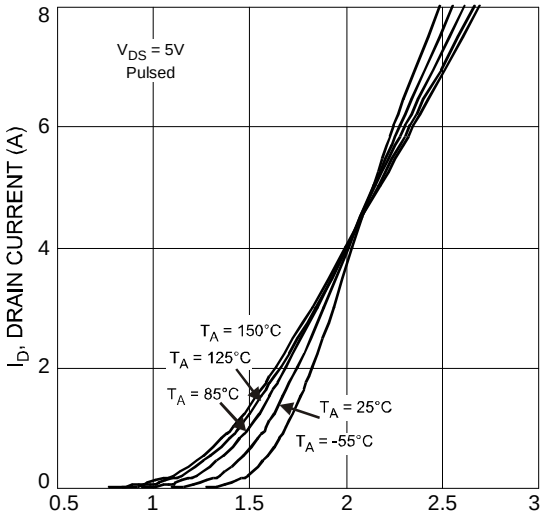


Fig. 2 Typical Transfer Characteristics

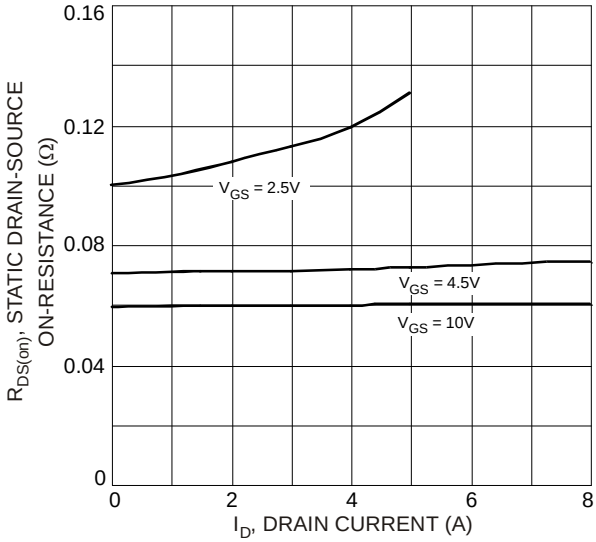


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

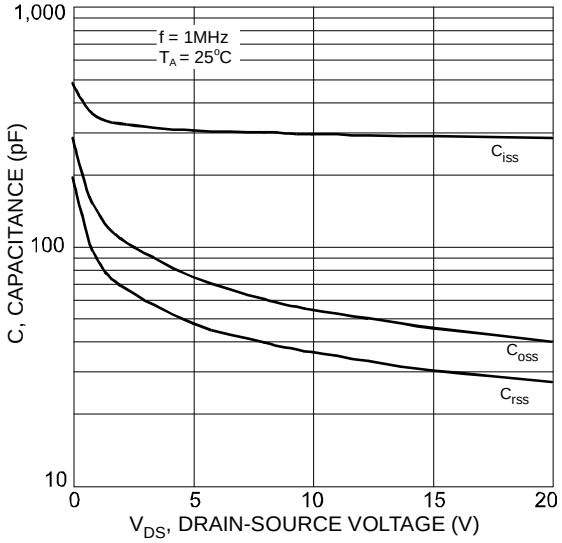


Fig. 4 Typical Total Capacitance

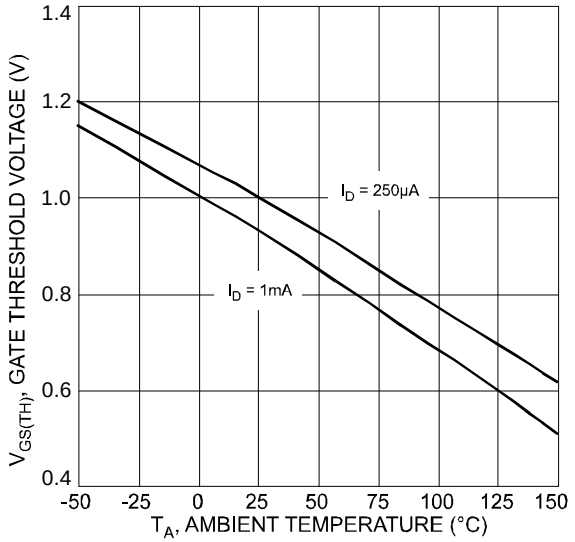


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

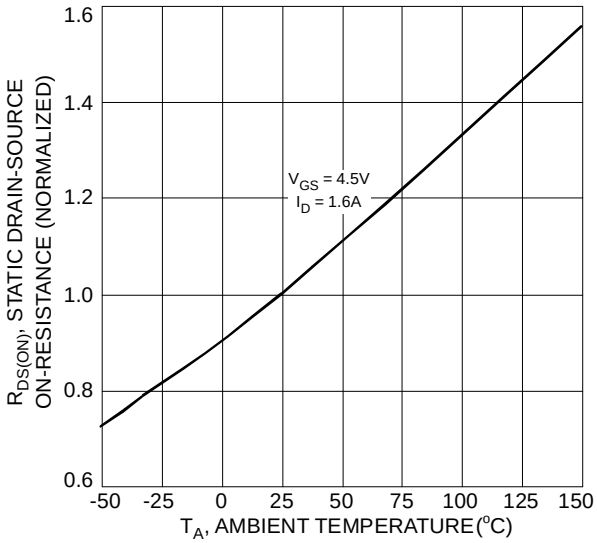


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

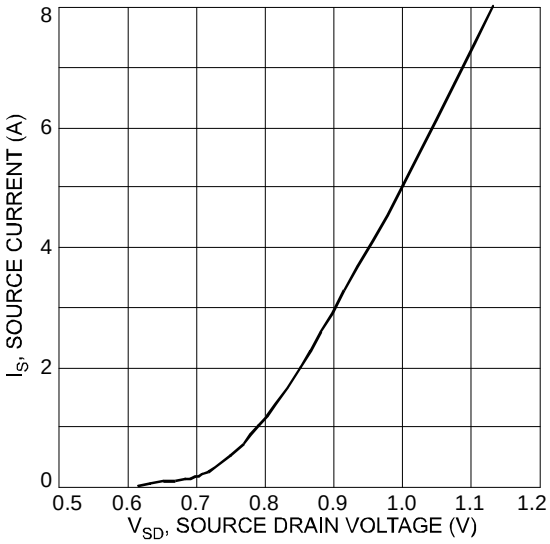


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

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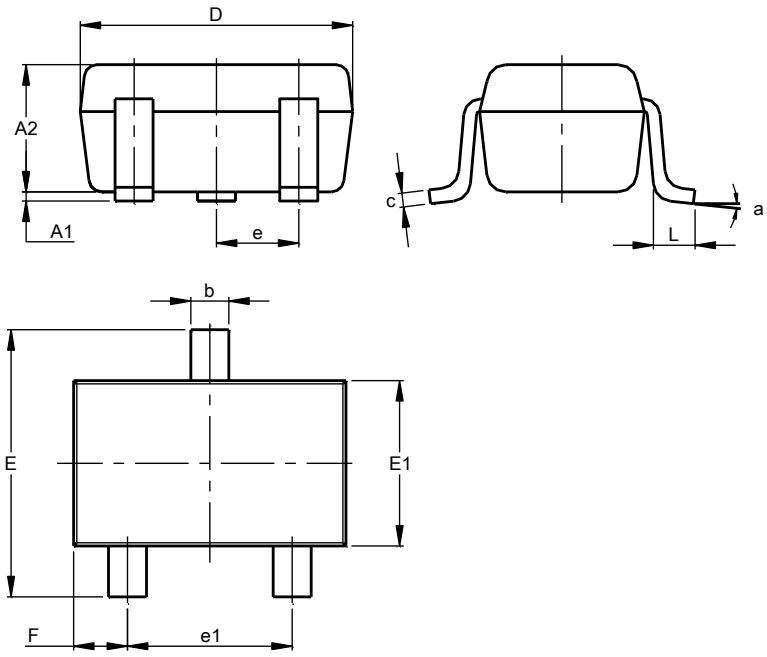
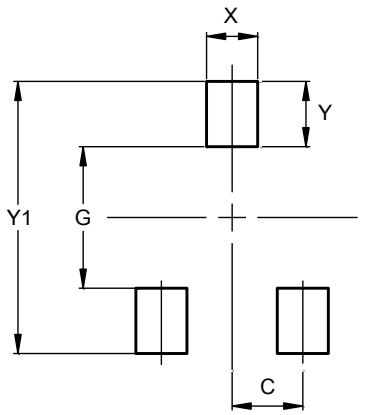


SOT323			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500